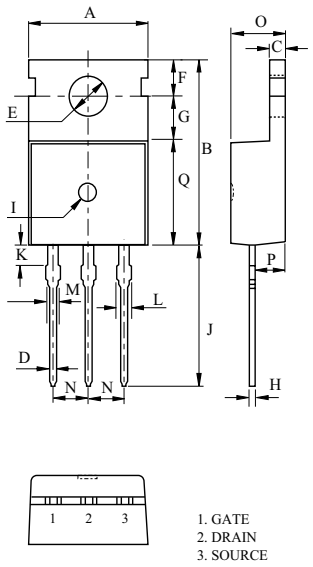
KMB050N60P

N CHANNEL MOS FIELD EFFECT TRANSISTOR

General Description

This planar stripe MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for active power factor correction , electronic lamp ballasts based on half bridge topology and switching mode power supplies.



DIM	MILLIMETERS
A	9.9± 0.2
B	15.95 MAX
C	1.3+0.1/-0.05
D	0.8± 0.1
E	ø 3.6 ±0.2
F	2.8± 0.1
G	3.7
H	0.5+0.1/-0.05
I	ø 1.5
J	13.08± 0.3
K	1.46
L	1.4± 0.1
M	1.27± 0.1
N	2.54± 0.2
O	4.5± 0.2
P	2.4± 0.2
Q	9.2± 0.2

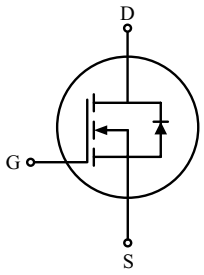
TO-220AB

FEATURES

- V_{DSS}= 60V, I_D= 50A
- Drain-Source ON Resistance :
  $R_{DS(ON)}$=0.022 Ω @V_{GS} = 10V
- Qg(typ.) = 32nC
- Improved dv/dt capacity, high Ruggedness
- Maximum Junction Temperature Range (175℃)

MAXIMUM RATING (Tc=25℃)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	@T_C=25℃	I_D	50	A
	@T_C=100℃		35	
	Pulsed (Note1)	I_{DP}	200	
Single Pulsed Avalanche Energy (Note 2)		E_{AS}	493	mJ
Repetitive Avalanche Energy (Note 1)		E_{AR}	12	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	7.0	V/ns
Drain Power Dissipation	Tc=25℃	P_D	120	W
	Derate above 25℃		0.8	W/℃
Maximum Junction Temperature		T_j	175	℃
Storage Temperature Range		T_{stg}	-55～175	℃
Thermal Characteristics				
Thermal Resistance, Junction-to-Case		R_{thJC}	1.24	℃/W
Thermal Resistance, Case-to-Sink		R_{thCS}	0.5	℃/W
Thermal Resistance, Junction-to-Ambient		R_{thJA}	62.5	℃/W



ELECTRICAL CHARACTERISTICS (Tc=25℃)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=250㎂, V_{GS}=0V	60	-	-	V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_j$	I_D=250㎂, Referenced to 25℃	-	0.07	-	V/℃
Drain Cut-off Current	I_{DSS}	V_{DS}=60V, V_{GS}=0V,	-	-	10	㎂
Gate Threshold Voltage	V_{th}	V_{DS}=V_{GS}, I_D=250㎂	2.0	-	4.0	V
Gate Leakage Current	I_{GSS}	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=25A	-	0.018	0.022	Ω
Dynamic						
Total Gate Charge	Q_g	V_{DS}= 48V, I_D= 50A V_{GS}=10V (Note4,5)	-	32	42	nC
Gate-Source Charge	Q_{gs}		-	8	-	
Gate-Drain Charge	Q_{gd}		-	12	-	
Turn-on Delay time	$t_{d(on)}$	V_{DD}= 30V I_D=25A R_G= 25 Ω (Note4,5)	-	20	50	ns
Turn-on Rise time	t_r		-	100	210	
Turn-off Delay time	$t_{d(off)}$		-	80	170	
Turn-off Fall time	t_f		-	85	180	
Input Capacitance	C_{iss}	V_{DS}=25V, V_{GS}=0V, f=1.0MHz	-	1050	1365	pF
Reverse Transfer Capacitance	C_{rss}		-	70	90	
Output Capacitance	C_{oss}		-	460	600	
Source-Drain Diode Ratings						
Continuous Source Current	I_S	V_{GS}<V_{th}	-	-	50	A
Pulsed Source Current	I_{SP}		-	-	200	
Diode Forward Voltage	V_{SD}	I_S=50A, V_{GS}=0V	-	-	1.5	V
Reverse Recovery Time	t_{rr}	I_S=50A, V_{GS}=0V, dIs/dt=100A/㎲	-	50	-	ns
Reverse Recovery Charge	Q_{rr}		-	70	-	㎌

Note 1) Repetivity rating : Pulse width limited by junction temperature.

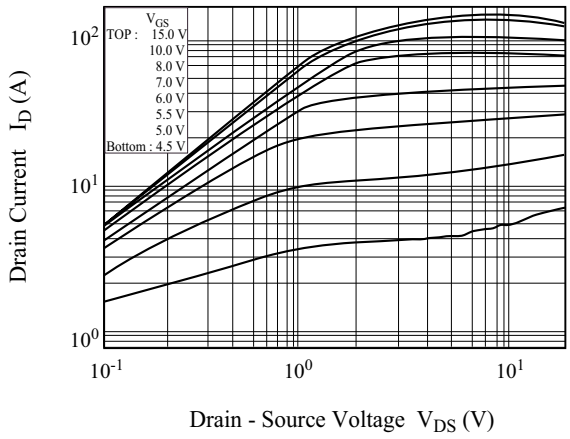
Note 2) L=230㎃, I_S=50A, V_{DD}=25V, R_G=25 Ω, Starting T_j=25℃.

Note 3) $I_S \leq$50A, dI/dt≤300A/㎲, $V_{DD} \leq BV_{DSS}$, Starting T_j=25℃.

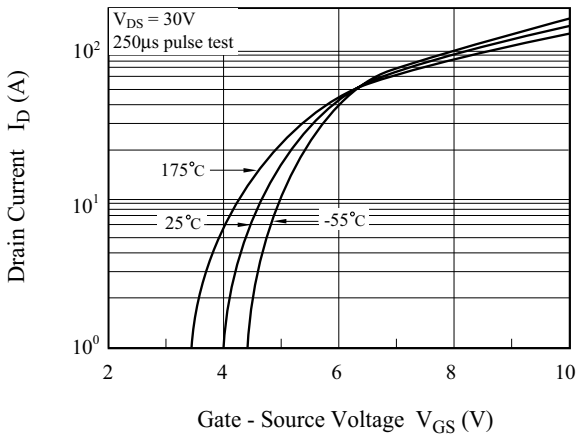
Note 4) Pulse Test : Pulse width ≤300㎲, Duty Cycle ≤2%.

Note 5) Essentially independent of operating temperature.

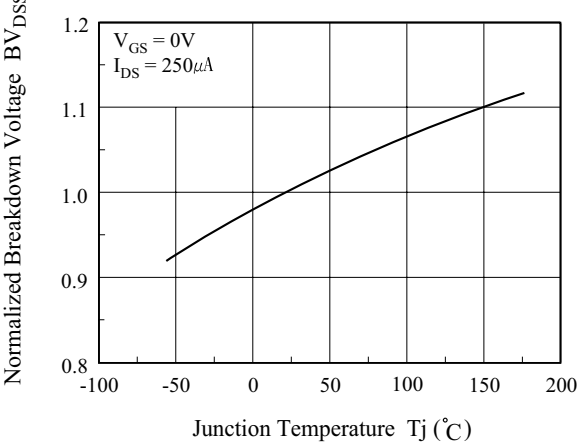
I_D - V_{DS}



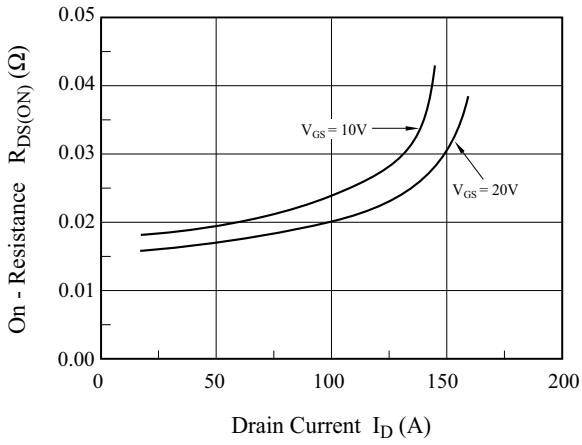
I_D - V_{GS}



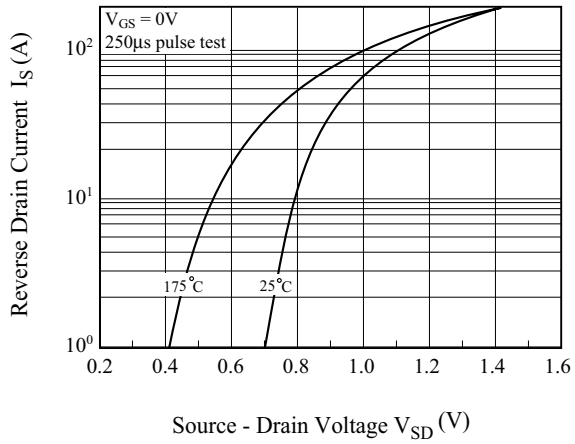
BV_{DSS} - T_j



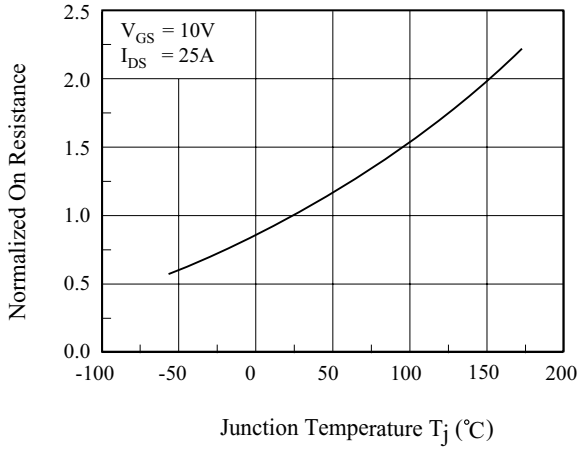
$R_{DS(ON)}$ - I_D



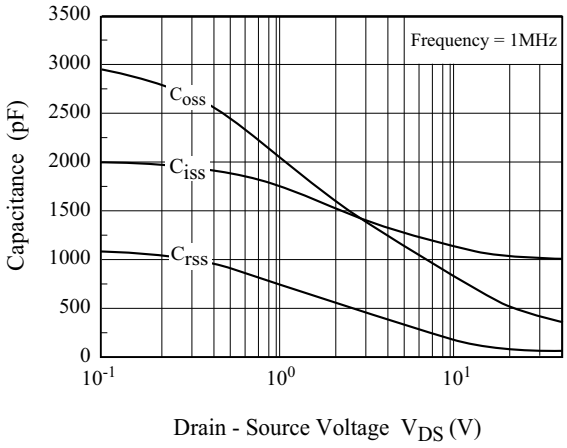
I_S - V_{SD}



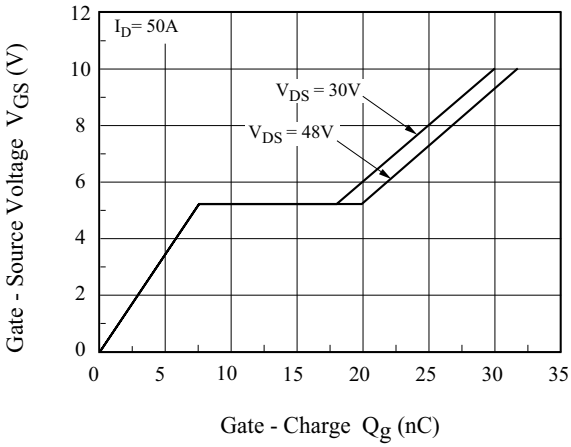
$R_{DS(ON)}$ - T_j



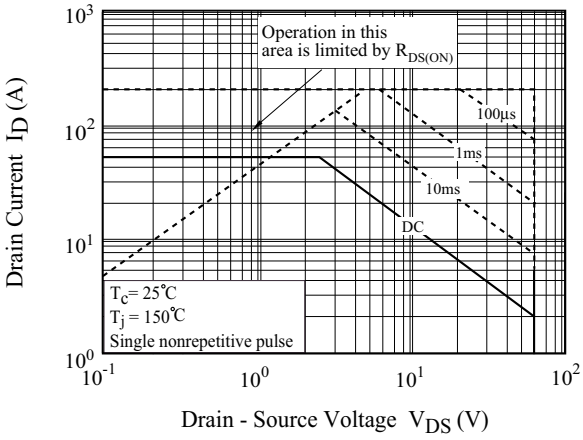
C - V_{DS}



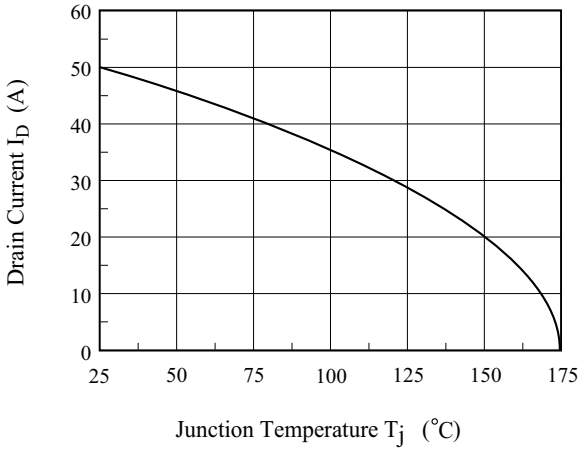
Q_g- V_{GS}



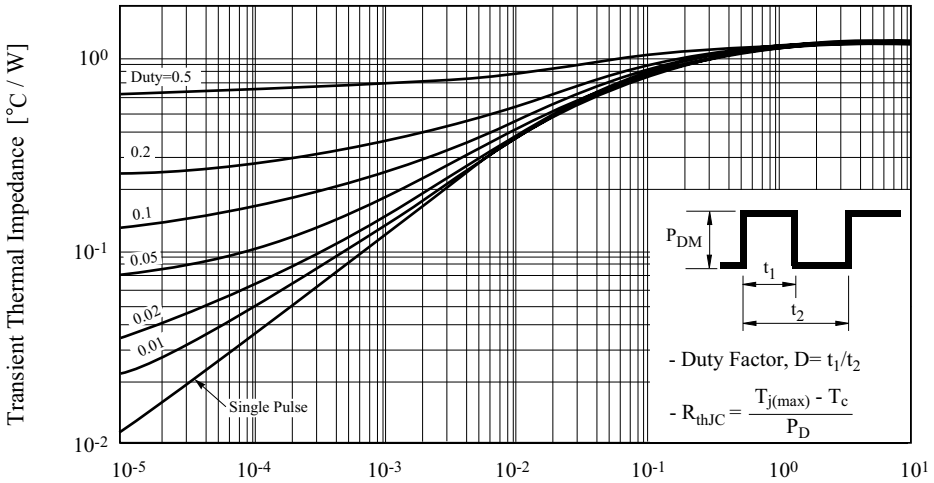
Safe Operation Area



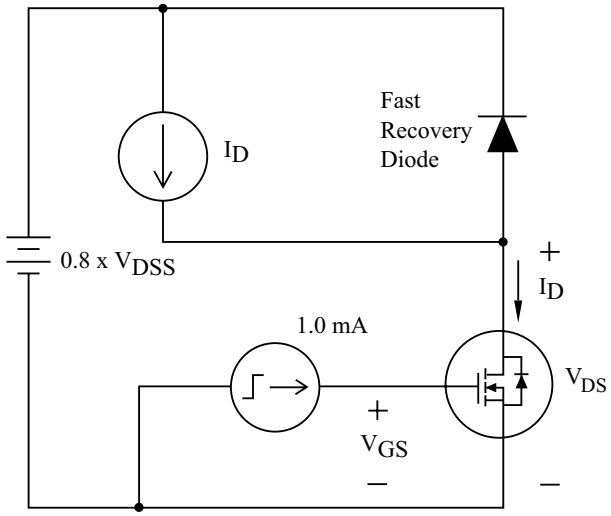
I_D - T_j

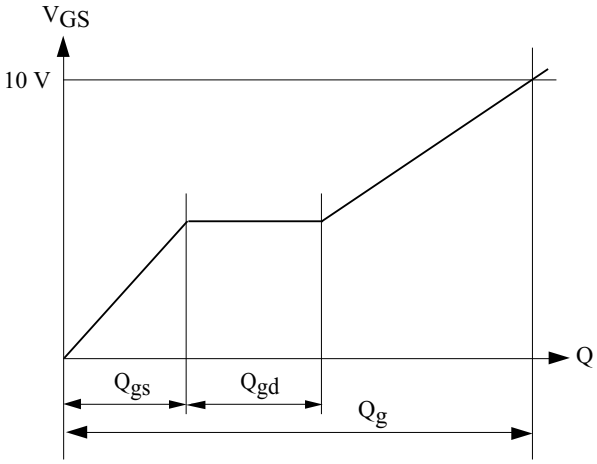


R_{th}

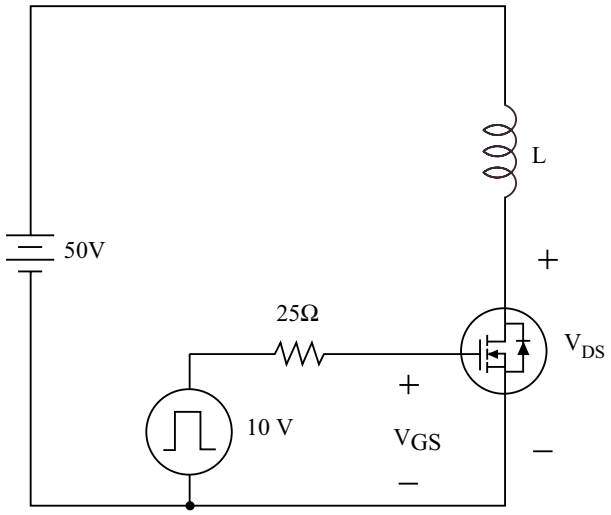


- Gate Charge

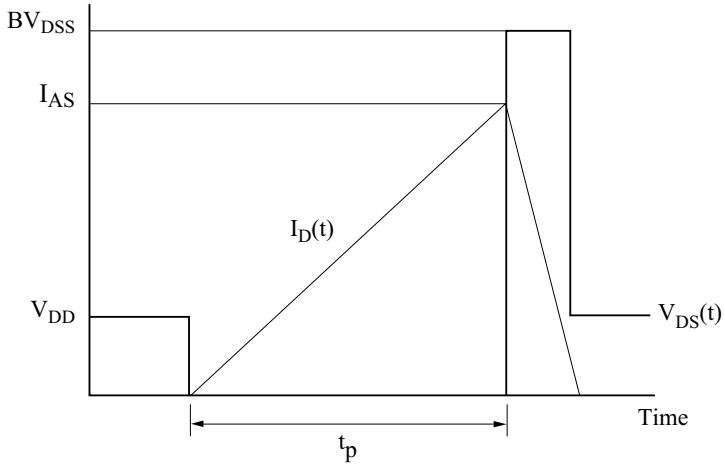




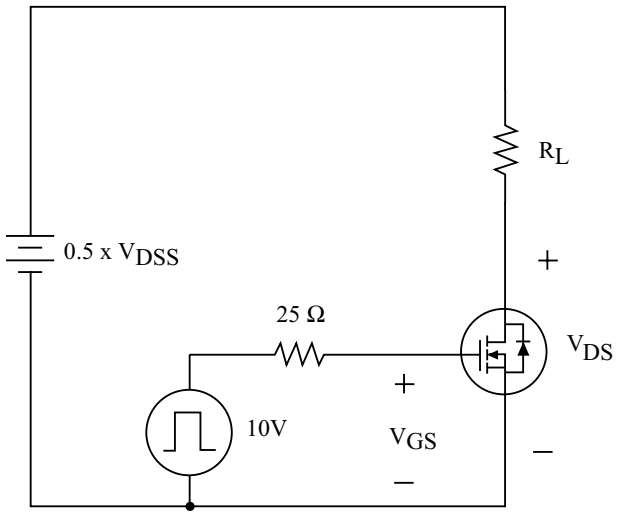
- Single Pulsed Avalanche Energy

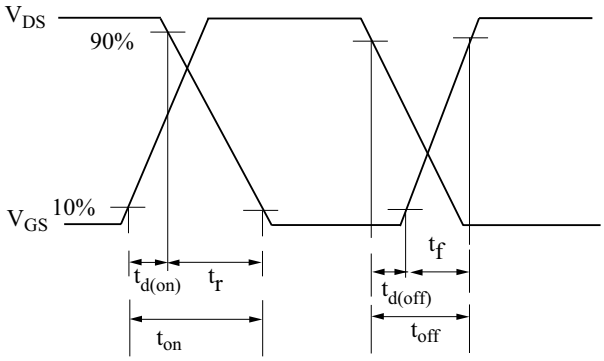


$$E_{AS}= \frac{1}{2} LI_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



- Resistive Load Switching





- Source - Drain Diode Reverse Recovery and dv /dt